



RLT1550-100G

TECHNICAL DATA



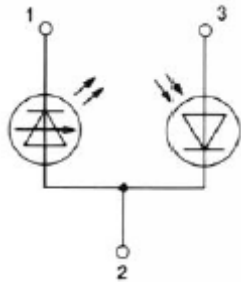
Infrared Laser Diode

Structure: **GaInAsP/InP, SQW structure**
 Lasing wavelength: **typ. 1580 nm, multi mode**
 Max. optical power: **100 mW**
 Package: **9 mm (SOT-148)**

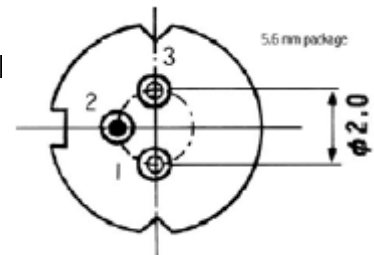
NOTE!
LASERDIODE
MUST BE COOLED!

ATTENTION
 OBSERVE PRECAUTIONS
 FOR HANDLING
 ELECTROSTATIC SENSITIVE DEVICE

PIN CONNECTION:



- 1) Laserdiode cathode
- 2) Laserdiode anode and photodiode cathode
- 3) Photodiode anode



Optical-Electrical Characteristics (Tc = 25°C)

| CHARACTERISTIC | SYMBOL | TEST CONDITION | MIN | TYP | MAX | UNIT |
|--------------------------|-----------------|-------------------------|-----|-------|------|---------|
| Optical Output Power | P _o | cw | - | 100 | - | mW |
| Threshold Current | I _{th} | cw | 300 | 400 | 600 | mA |
| Operation Current | I _{op} | P _o = 100 mW | 700 | 800 | 1000 | mA |
| Operation Voltage | V _{op} | P _o = 100 mW | 2.3 | 2.4 | 2.5 | V |
| Lasing Wavelength | λ _p | P _o = 100 mW | - | 1580 | 1582 | nm |
| Spectra halfwidth (FWHM) | Δλ | P _o = 100 mW | 3 | 4 | 6 | nm |
| Beam Divergence | Θ | P _o = 100 mW | 8 | 10 | 12 | ° |
| Beam Divergence | Θ | P _o = 100 mW | 43 | 45 | 47 | ° |
| Emitting area | Wxd | | - | 100x1 | - | μm x μm |